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SEMICONDUCTOR

### November 2013

FQPF2N70 — N-Channel QFET<sup>®</sup> MOSFET

## FQPF2N70

### **N-Channel QFET<sup>®</sup> MOSFET** 700 V, 2.0 A, 6.3 Ω

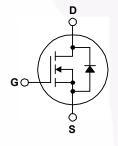
### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

### Features

- 2.0 A, 700 V,  $R_{DS(on)}$  = 6.3  $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 1.0 A
- Low Gate Charge (Typ. 9 nC)
- Low Crss (Typ. 5 pF)
- 100% Avalanche Tested





### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

Symbol	Parameter Drain-Source Voltage		FQPF2N70	0 Unit V	
V <sub>DSS</sub>			700		
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°C)		2.0*	Α
		- Continuous (T <sub>C</sub> = 100°C)		1.3*	Α
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	8.0*	А
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energ	ах	(Note 2)	140	mJ
I <sub>AR</sub>	Avalanche Current (Not		(Note 1)	2.0	Α
E <sub>AR</sub>	Repetitive Avalanche Energy (Note		(Note 1)	2.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		(Note 3)	4.5	V/ns
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C)		28	W
		- Derate Above 25°C		0.22	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
ΤL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		onds	300	°C

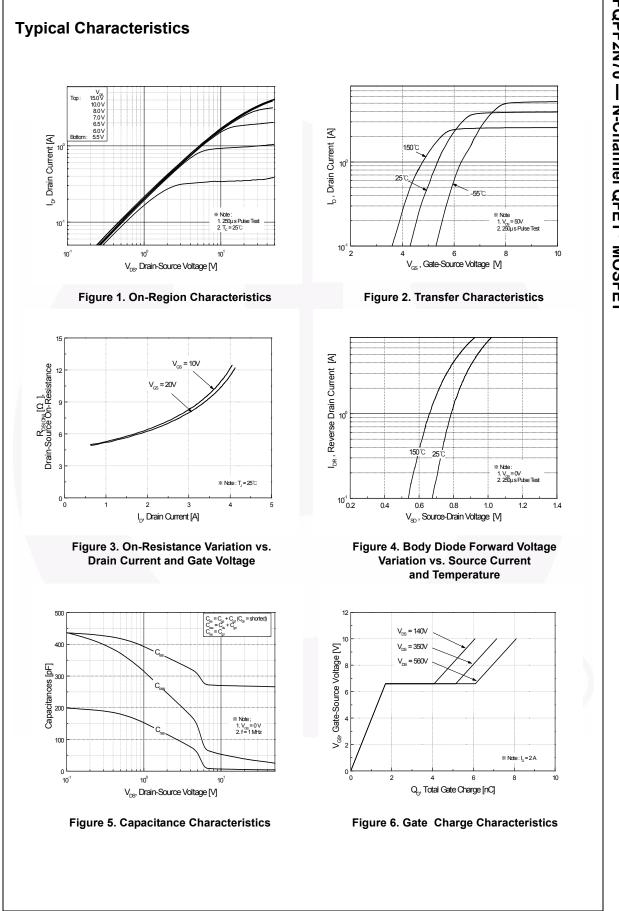
\*Drain current limited by maximum junction temperature.

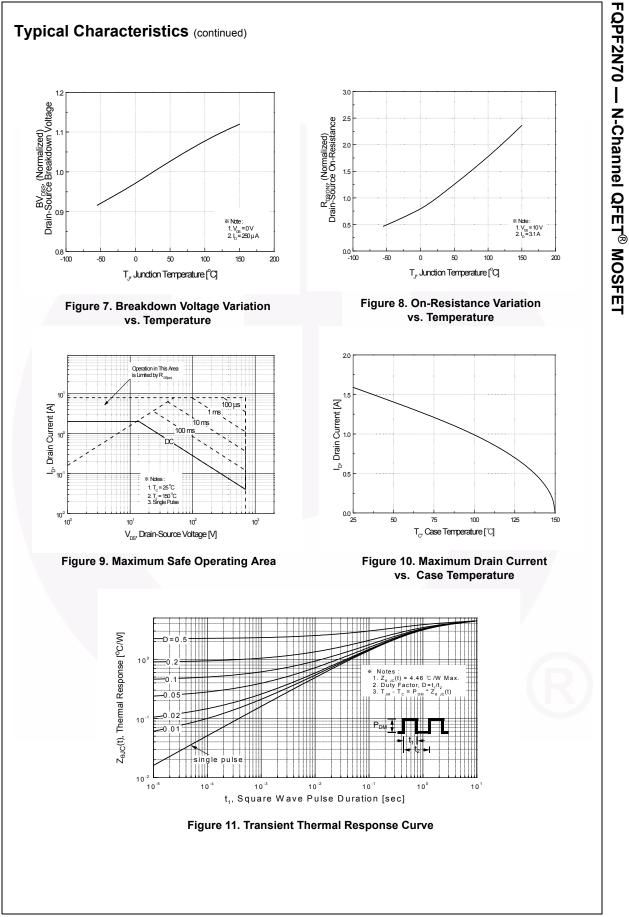
### **Thermal Characteristics**

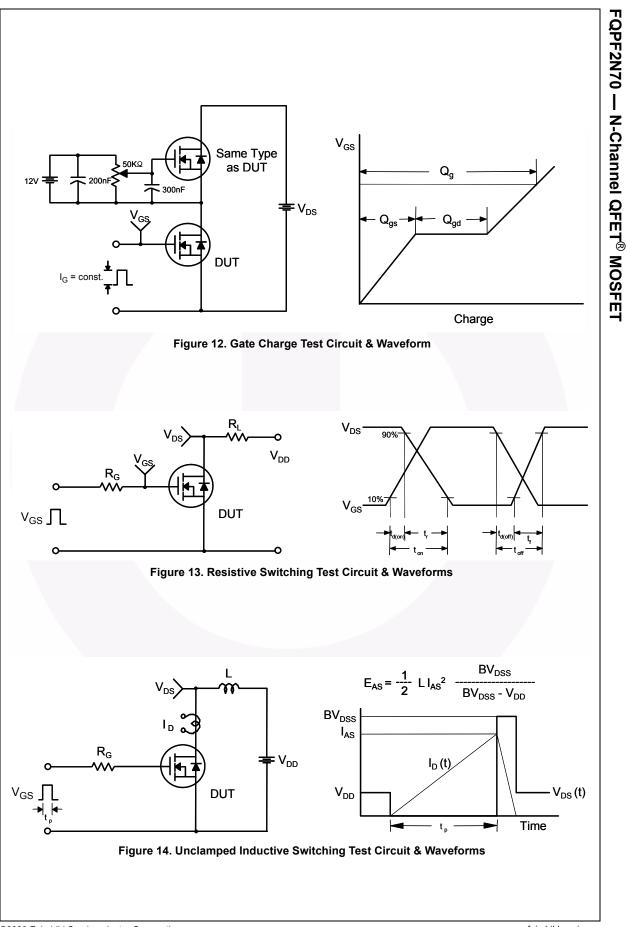
Symbol	Parameter	FQPF2N70	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	4.46	4.46 °C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5		

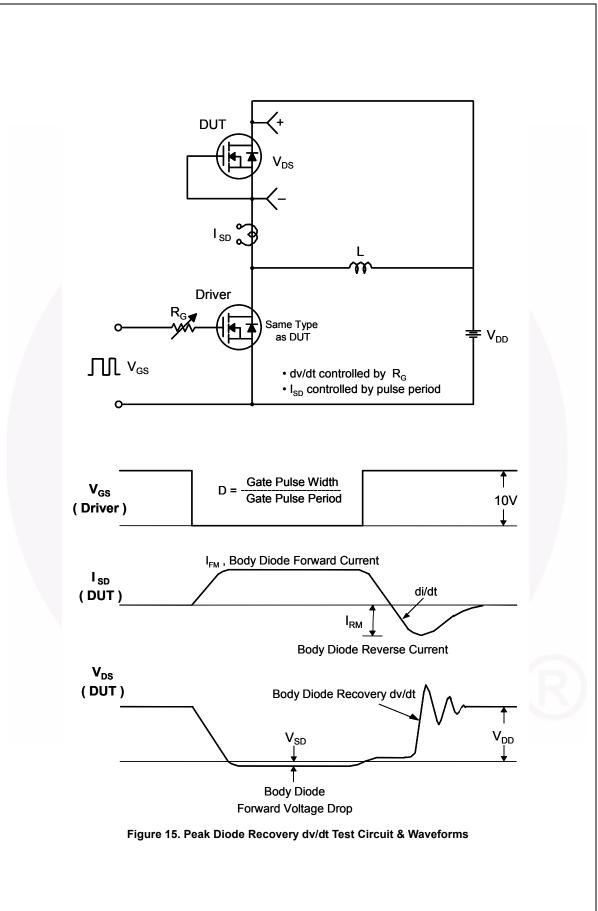
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acteristics apacitance		V <sub>DS</sub> = 50 V, I <sub>D</sub> = 1.0 A	A			1	
apacitance					2.45		S
•					270	350	pF
Capacitance		V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz			38	50	pF
e Transfer Capacitance	_	t = 1.0 MHZ			5	7	pF
	-				Ŭ	· ·	pi
aracteristics							
n Delay Time						30	ns
n Rise Time		$V_{DD} = 350 \text{ V}, \text{ I}_{D} = 2.0 \text{ A},$ $R_{G} = 25 \Omega$ (Note 4) $V_{DS} = 560 \text{ V}, \text{ I}_{D} = 2.0 \text{ A},$				80	ns
f Delay Time						50	ns
f Fall Time						70	ns
ate Charge					8.1	11	nC
ource Charge					1.7		nC
rain Charge		1			4.4		nC
	-						
			ngs		1		
m Continuous Drain-S	Source Dio	de Forward Current				2.0	A
m Pulsed Drain-Sourc	e Diode Fo					8.0	A
	Voltage				-	1.4	V
e Recovery Time		00 0	,		260		ns
Recovery Charge		dI <sub>F</sub> / dt = 100 A/µs		-	1.09		μC
	ite Charge ource Charge ain Charge <b>Diode Characteri</b> m Continuous Drain-S m Pulsed Drain-Source ource Diode Forward <sup>1</sup>	te Charge ource Charge ain Charge Diode Characteristics an m Continuous Drain-Source Dio m Pulsed Drain-Source Diode F- ource Diode Forward Voltage e Recovery Time	te Charge $V_{DS} = 560 \text{ V}, \text{ I}_D = 2.0 \text{ V}_{GS} = 10 \text{ V}$ surce Charge $V_{GS} = 10 \text{ V}$ ain Charge <b>Diode Characteristics and Maximum Rati</b> m Continuous Drain-Source Diode Forward Currentm Pulsed Drain-Source Diode Forward Currentburce Diode Forward Voltage $V_{GS} = 0 \text{ V}, \text{ I}_S = 2.0 \text{ A}$ Recovery Time $V_{GS} = 0 \text{ V}, \text{ I}_S = 2.0 \text{ A}$	Interview       V <sub>DS</sub> = 560 V, I <sub>D</sub> = 2.0 A,         burce Charge       V <sub>GS</sub> = 10 V         ain Charge       (Note 4)         Diode Characteristics and Maximum Ratings         m Continuous Drain-Source Diode Forward Current         m Pulsed Drain-Source Diode Forward Current         purce Diode Forward Voltage         V <sub>GS</sub> = 0 V, I <sub>S</sub> = 2.0 A         Recovery Time	Truin finite $V_{DS}$ = 560 V, $I_D$ = 2.0 A,          burce Charge $V_{GS}$ = 10 V          ain Charge       (Note 4)          Diode Characteristics and Maximum Ratings          m Continuous Drain-Source Diode Forward Current          m Pulsed Drain-Source Diode Forward Current          purce Diode Forward Voltage $V_{GS}$ = 0 V, $I_S$ = 2.0 A          e Recovery Time $V_{GS}$ = 0 V, $I_S$ = 2.0 A,	Truin finite $V_{DS} = 560 \text{ V}, \text{ I}_D = 2.0 \text{ A},$ 8.1burce Charge $V_{GS} = 10 \text{ V}$ 1.7ain Charge(Note 4)4.4Diode Characteristics and Maximum Ratingsm Continuous Drain-Source Diode Forward Currentm Pulsed Drain-Source Diode Forward Currentm Pulsed Drain-Source Diode Forward Currentource Diode Forward Currente Recovery Time $V_{GS} = 0 \text{ V}, \text{ I}_S = 2.0 \text{ A},$ 260	Truin finite $V_{DS} = 560 \text{ V}, I_D = 2.0 \text{ A},$ 8.1       11         nurce Charge $V_{GS} = 10 \text{ V}$ 1.7          ain Charge $V_{GS} = 10 \text{ V}$ 4.4          Diode Characteristics and Maximum Ratings         m Continuous Drain-Source Diode Forward Current         2.0         m Pulsed Drain-Source Diode Forward Current         8.0         purce Diode Forward Voltage $V_{GS} = 0 \text{ V}, I_S = 2.0 \text{ A},$ 1.4         Recovery Time $V_{GS} = 0 \text{ V}, I_S = 2.0 \text{ A},$ 260

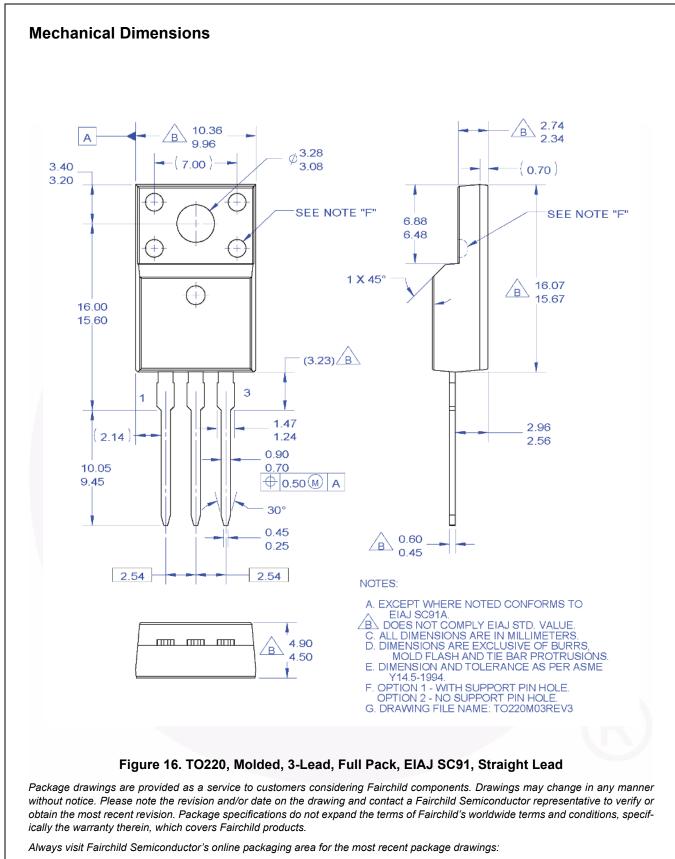








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FQPF2N70 — N-Channel QFET<sup>®</sup> MOSFET



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